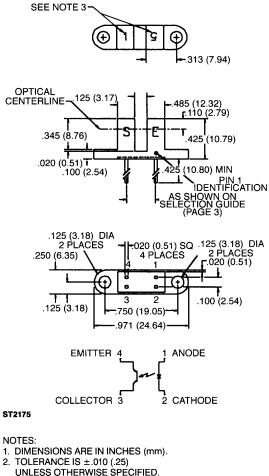


QVB SERIES

PACKAGE DIMENSIONS



- UNLESS OTHERWISE SPECIFIED. 3. NUMBER INDICATES APERTURE SIZE.
- (5 = .050'', 1 = .010'')

DESCRIPTION

The QVB series of switches is designed to allow the user maximum flexibility in applications. Each switch consists of an infrared emitting diode facing an NPN photo-transistor across a .125" (3.18 mm) gap. A unique housing design provides a smooth external surface to prevent dust and dirt buildup while molded internal apertures give precise positioning and also provide protection from ambient light interference.



- Ambient light and dust protection.
- Lead spacing available at .220", .300", or .320".
- .050" and .010" aperatures available.



SEMICONDUCTOR

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C U	Inless Otherwise Specified)
Storage Temperature	
	-40° C to $+85^{\circ}$ C
Soldering: Lead Temperature (Iron) Lead Temperature (Flow)	
INPUT DIODE	
Continuous Forward Current	
Reverse Voltage Power Dissipation	
OUTPUT TRANSISTOR	
Collector-Emitter Voltage	
Emitter-Collector Voltage	
Power Dissipation	

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}$ C Unless Otherwise Specified)							
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS	
INPUT DIODE Forward voltage	V _F	_		1.70	v	l _F = 20 mA	
Reverse Leakage Current	l _e	_		100	μA	$V_{R} = 2.0 V$	
OUTPUT TRANSISTOR Emitter-Collector Breakdown	BV _{ECO}	5			V	$I_{\rm E} = 100 \ \mu {\rm A}, {\rm Ee} = 0$	
Collector-Emitter Breakdown	BV _{CEO}	30			V	I _c = 1.0 mA, Ee = 0	
Collector-Emitter Leakage	CEO			100	nA	$V_{ce} = 10.0 V, Ee = 0$	
COUPLED On-State Collector Current		See selection guide page 3.		mA	$I_{\rm F} = 20$ mA, $V_{\rm CE} = 5$ V		
Saturation Voltage		_		0.40	V	$I_{\rm F} = 20 {\rm mA}, I_{\rm c} = 0.1 {\rm mA}$	

NOTES

Derate power dissipation linearly 1.67 mW/°C above 25°C.
 RMA flux is recommended.

- Methanol or Isopropanol alcohols are recommended as cleaning agents.
 Soldering iron tip ¼e" (1.6 mm) from housing.



PART NUMBER	LEAD SPACING	APER	TURES		
		LED	SENSOR	MIN	MAX
QVB11123	.220″	0.050"	0.010"	0.20	—
QVB11124	.220″	0.050″	0.010″	0.50	
QVB11223	.300″	0.050"	0.010″	0.20	_
QVB11224	.300″	0.050″	0.010"	0.50	—
QVB11323	.320″	0.050″	0.010"	0.20	
QVB11324	.320″	0.050″	0.010"	0.50	-
QVB11133	.220″	0.050"	0.050″	0.50	_
QVB11134	.220″	0.050″	0.050″	1.00	—
QVB11233	.300″	0.050″	0.050"	0.50	_
QVB11234	.300″	0.050″	0.050″	1.00	—
QVB11333	.320″	0.050"	0.050″	0.50	
QVB11334	.320″	0.050″	0.050"	1.00	
QVB21113	.220″	0.010″	0.010"	0.10	_
QVB21114	.220″	0.010″	0.010"	0.20	_
QVB21213	.300″	0.010″	0.010″	0.10	
QVB21214	.300″	0.010"	0.010″	0.20	-
QVB21313	.320″	0.010"	0.010"	0.10	_
QVB21314	.320″	0.010"	0.010"	0.20	_



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